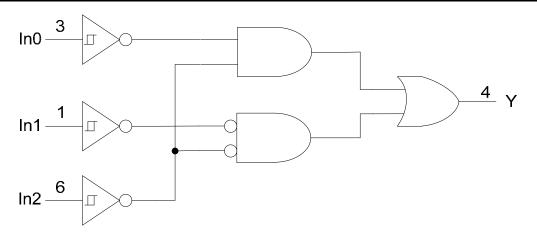


Pin Descriptions

Pin Name	Function
IN1	Data Input
GND	Ground
IN0	Data Input
Υ	Data Output
Vcc	Supply Voltage
IN2	Data Input

Logic Diagram

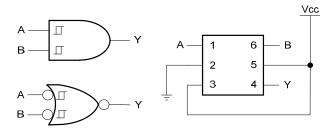


Function Table

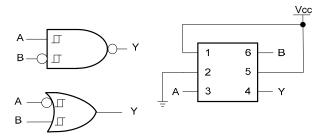
	Inputs	Output	
IN2	IN1	IN0	Y
L	L	L	Н
L	L	Н	L
L	Н	L	Н
L	Н	Н	L
Н	L	L	L
Н	L	Н	L
Н	Н	L	Н
Н	Н	Н	Н



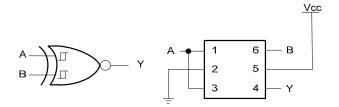
Logic Configurations



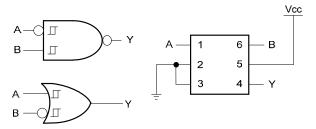
Configuration 1
2-Input AND Gate
2-Input NOR Gate with Both Inputs Inverted



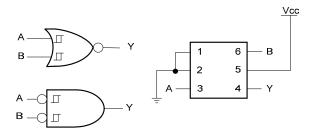
Configuration 3
2-Input NAND Gate with B Input Inverted
2-Input OR Gate with A Input Inverted



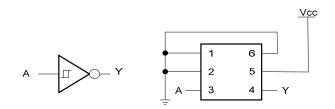
Configuration 5
2-Input XNOR Gate



Configuration 2
2-Input NAND Gate with A Input Inverted
2-Input OR Gate with B input Inverted



Configuration 4
2-Input NOR Gate
2-Input AND Gate with Both Inputs Inverted



Configuration 6 Inverter

Function Selection Table							
Logic Function	Configuration						
2-input AND	1						
2-input AND with both inputs inverted	4						
2-input NAND with inverted input	2, 3						
2-input OR with inverted input	2, 3						
2-input NOR	4						
2-input NOR with both inputs inverted	1						
2-input XNOR	5						
1-input INVERTER	6						



Absolute Maximum Ratings (Note 4)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +6.5	V
VI	Input Voltage Range	-0.5 to +6.5	V
Vo	Voltage applied to output in high impedance or I _{OFF} state	-0.5 to +6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
l _{IK}	Input Clamp Current V _I <0	-50	mA
lok	Output Clamp Current	-50	mA
Io	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 5)

Symbol		Parameter	Min	Max	Unit
	On and Care Mallana	Operating	1.65	5.5	V
V _{CC}	Operating Voltage	Data retention only	1.5		V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	Vcc	V
		V _{CC} = 1.65V		-4	
		V _{CC} = 2.3V		-8	
Іон	High-level output current			-16	mA
		$V_{CC} = 3V$		-24	
		V _{CC} = 4.5V		-32	
		V _{CC} = 1.65V		4	
		V _{CC} = 2.3V		8	
I_{OL}	Low-level output current			16	mA
		V _{CC} = 3V		24	
		V _{CC} = 4.5V		32	
		V _{CC} = 1.8V ± 0.15V, 2.5V ± 0.2V		20	
Δt/ΔV	Input transition rise or fall rate	V _{CC} = 3.3V ± 0.3V		10	ns/V
		V _{CC} = 5V ± 0.5V		5	
T _A	Operating free-air temperature		-40	+125	°C

Notes: 5. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics $T_A = -40$ °C to +85°C (All typical values are at $V_{CC} = 3.3V$, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit
			1.65V	0.70		1.20	
	Positive-going input threshold voltage		2.3V	1.11		1.60	
V_{T+}			3V	1.50		2.00	
			4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.72	
			2.3V	0.58		1.00	
V_{T-}	Negative-going input		3V	0.80		1.30	
	threshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
			2.3V	0.40		0.80	
ΔV_T	Hysteresis		3V	0.35		1.00	
	(V _{T+} - V _{T-)}		4.5V	0.55		1.10	
			5.5V	0.60		1.20	
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} -0.1			
		$I_{OH} = -4mA$	1.65V	1.2			
V	11.11	$I_{OH} = -8mA$	2.3V	1.9			\ /
V_{OH}	High Level Output Voltage	I _{OH} = -16mA	0)/	2.4			V
		I _{OH} = -24mA	3V	2.3			
		I _{OH} = -32mA	4.5V	3.8			
		$I_{OL} = 100 \mu A$	1.65V to 5.5V			0.1	
		I _{OL} = 4mA	1.65V			0.45	
V	LP ob Towal Lond Wolfe or	I _{OL} = 8mA	2.3V			0.3	
V_{OL}	High-level Input Voltage	I _{OL} = 16mA	0)/			0.4	V
		$I_{OL} = 24mA$	3V			0.55	
		$I_{OL} = 32mA$	4.5V			0.55	
lı	Input Current	V _I = 5.5V or GND	0 to 5.5V			±5	μΑ
I _{OFF}	Power Down Leakage Current	V_I or $V_O = 5.5V$	0			± 10	μΑ
Icc	Supply Current	V _I = 5.5V of GND I _O =0	1.65V to 5.5V			10	μΑ
Δl _{CC}	Additional Supply Current	One input at V _{CC} -0.6V Other inputs at V _{CC} or GND	3V to 5.5V			500	μА



Electrical Characteristics $T_A = -40^{\circ}C$ to +125°C (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}C$)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
V_{T+}	Positive-going input threshold voltage		3V	1.50		2.00	
	tilleshold voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.75	
			2.3V	0.58		1.03	
V_{T-}	Negative-going input threshold voltage		3V	0.80		1.33	
	tillesiloid voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
			2.3V	0.37		0.80	
ΔV_{T}	Hysteresis		3V	0.32		1.00	
	(V _{T+} - V _{T-)}		4.5V	0.50		1.20	
			5.5V	0.55		1.40	
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} -0.1			
		I _{OH} = -4mA	1.65V	0.95			
.,		I _{OH} = -8mA	2.3V	1.7			.,
V_{OH}	High Level Output Voltage	I _{OH} = -16mA	0) /	1.9			V
		I _{OH} = -24mA	3V	2.0			
		I _{OH} = -32mA	4.5V	3.4			
		I _{OL} = 100μA	1.65V to 5.5V			0.1	
		I _{OL} = 4mA	1.65 V			0.7	
		I _{OL} = 8mA	2.3V			0.45	.,
V_{OL}	High-level Input Voltage	I _{OL} = 16mA	21.			0.6	V
		I _{OL} = 24mA	3V			0.8	
		I _{OL} = 32mA	4.5V			0.8	
II	Input Current	V _I = 5.5 V or GND	0 to 5.5V			± 100	μA
l _{OFF}	Power Down Leakage Current	V_I or $V_O = 5.5V$	0			± 200	μA
Icc	Supply Current	V _I = 5.5V of GND I _O =0	1.65V to 5.5V			200	μΑ
ΔI _{CC}	Additional Supply Current	One input at V _{CC} –0.6V Other inputs at V _{CC} or GND	3V to 5.5V			5000	μА



Package Characteristics (All typical values are at $V_{CC} = 3.3V$, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit	
CI	Input Capacitance	$V_I = V_{CC} - \text{or GND}$	3.3		3.5		pF	
		SOT26			204			
	Thermal Resistance Junction-	SOT363	(Note 6)		371		00.00	
θ_{JA}	to-Ambient	X2-DFN1410-6			430		°C/W	
		X2-DFN1010-6			510			
	SOT26			52				
	Thermal Resistance Junction-	SOT363	(Note 6)		143		°C/W	
θ _{JC}	to-Case	X2-DFN1410-6			190			
		X2-DFN1010-6			250			

Notes:

Switching Characteristics

 $T_A = -40$ °C to +85°C, $C_L = 30$ or 50pF as noted (see Figure 1)

Parameter From (Input)	TO (OUTPUT)		: 1.8V .15V		= 2.5V).2V	~ ~	: 3.3V).3V	V _{CC}	= 5V .5V	Unit	
	(input)	it) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Υ	1.0	14.4	0.7	8.3	0.7	6.3	0.7	5.1	ns

 $T_A = -40$ °C to +125°C, $C_L = 30$ or 50pF as noted (see Figure 1)

Parameter From	TO (OUTPUT)	± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit	
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Y	1.0	18.0	0.7	10.4	0.7	7.9	0.7	6.4	ns

Operating Characteristics

$T_A = +25^{\circ}C$

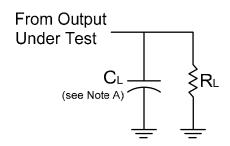
	Parameter	Test Conditions	Vcc = 1.8V Typ.	Vcc = 2.5V Typ.	Vcc = 3.3V Typ.	Vcc = 5V Typ.	Unit
C _{pd}	Power dissipation capacitance	f = 10 MHz	22	22	23	24	pF

^{6.} Test condition for SOT26, SOT363, X2-DFN1410-6 and X2-DFN1010-6: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Propagation Delay Times
Inverting and Non Inverting Outputs

Parameter Measurement Information



V	Inj	outs	V		R _L	
V _{CC}	VI	t _r /t _f	V _M	CL		
1.8V ±0.15V	V _{CC}	≤ 2ns	V _{CC} /2	30pF	1ΚΩ	
2.5V ±0.2V	V _{CC}	≤ 2ns	V _{CC} /2	30pF	500Ω	
3.3V ±0.3V	3V	≤ 2.5ns	1.5V	50pF	500Ω	
5V ±0.5V	V _{CC}	≤ 2.5ns	V _{CC} /2	50pF	500Ω	

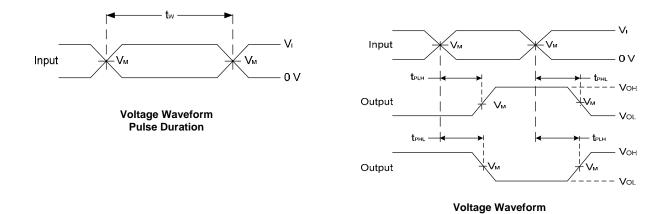


Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

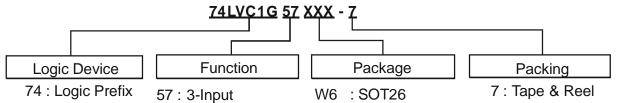
B. All pulses are supplied at pulse repetition rate ≤ 10 MHz

C. Inputs are measured separately one transition per measurement

D. t_{PLH} and t_{PHL} are the same as t_{PD}



Ordering Information



LVC: 1.65 to 5.5V Configurable DW: SOT363

Family Multiple-Function FW4: X2-DFN1010-6 1G: One gate Gate FZ4: X2-DFN1410-6

	Davida	Davidson On de	Packaging	7" Tape and Reel	
	Device	Package Code	(Note 7)	Quantity	Part Number Suffix
9	74LVC1G57W6-7	W6	SOT26	3000/Tape & Reel	-7
Pb	74LVC1G57DW-7	DW	SOT363	3000/Tape & Reel	-7
Pb	74LVC1G57FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7
Pb.	74LVC1G57FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7

Notes: 7. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Marking Information

(1) SOT26, SOT363



2

3

XX: Identification code

Y: Year 0~9

W: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week

X: A~Z: Internal Code

Part Number	Package	Identification Code
74LVC1G57W6	SOT26	TW
74LVC1G57DW	SOT363	TW

(2) X2-DFN1010-6, X2-DFN1410-6

(Top View)

XX XX: Identification Code

 $\overline{\underline{Y}}$: Year : 0~9

\overline{\text{\Week}}: A~Z : 1~26 week; a~z : 27~52 week; z represents

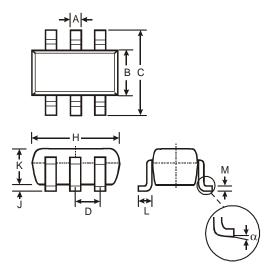
52 and 53 week \underline{X} : A~Z: Internal code

Part Number	Package	Identification Code
74LVC1G57FW4	X2-DFN1010-6	TW
74LVC1G57FZ4	X2-DFN1410-6	TW



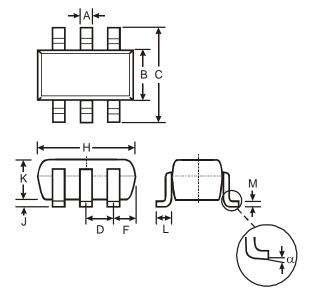
Package Outline Dimensions (All Dimensions in mm)

(1) SOT26



SOT26				
Dim	Min	Max	Тур	
Α	0.35	0.50	0.38	
В	1.50	1.70	1.60	
C	2.70	3.00	2.80	
D	_	_	0.95	
Н	2.90	3.10	3.00	
7	0.013	0.10	0.05	
K	1.00	1.30	1.10	
L	0.35	0.55	0.40	
M	0.10	0.20	0.15	
α	0°	8°	_	
All Dimensions in mm				

(2) SOT363



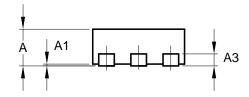
SOT363				
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
O	2.00	2.20		
D	0.65 Typ			
F	0.40	0.45		
H	1.80	2.20		
۲	0	0.10		
K	0.90	1.00		
Г	0.25	0.40		
М	0.10	0.22		
α	0°	8°		
All Dimensions in mm				

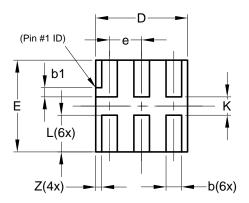
Downloaded from **Arrow.com.**



Package Outline Dimensions (All Dimensions in mm)

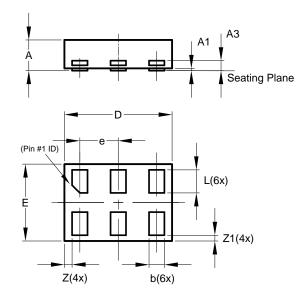
(3) X2-DFN1010-6





X2-DFN1010-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A 1	0.00	0.05	0.02	
A3		_	0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
е	_	_	0.35	
٦	0.35	0.45	0.40	
K	0.15		_	
Z			0.065	
All Dimensions in mm				

(4) X2-DFN1410-6

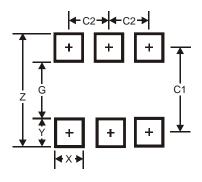


X2-DFN1410-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3		_	0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е		_	0.50	
L	0.25	0.35	0.30	
Z	_	_	0.10	
Z 1	0.045	0.105	0.075	
All Dimensions in mm				



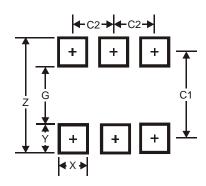
Suggest Pad Layout

(1) SOT26



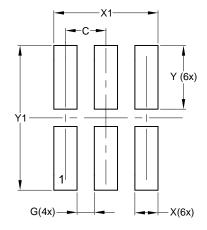
Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

(2) SOT363



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

(3) X2-DFN1010-6

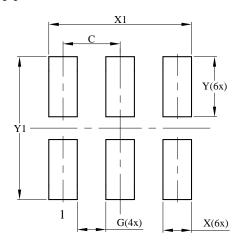


Dimensions	Value (in mm)
C	0.350
G	0.150
Х	0.200
X1	0.900
Y	0.550
Y1	1.250



Suggest Pad Layout

(4) X2-DFN1410-6



Dimensions	Value	
Dillielisions	(in mm)	
С	0.500	
G	0.250	
Х	0.250	
X1	1.250	
Y	0.525	
Y1	1.250	



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